Dual General Purpose Transistor

The NST3904DXV6T1G device is a spin-off of our popular SOT-23/SOT-323 three-leaded device. It is designed for general purpose amplifier applications and is housed in the SOT-563 six-leaded surface mount package. By putting two discrete devices in one package, this device is ideal for low-power surface mount applications where board space is at a premium.

Features

- h_{FE}, 100-300
- Low $V_{CE(sat)}$, $\leq 0.4 \text{ V}$
- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- AEC-Q101 Qualified and PPAP Capable NSVT3904DXV6T1G, SNST3904DXV6T5G
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These are Pb-Free Devices

MAXIMUM RATINGS

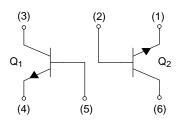
Rating		Symbol	Value	Unit
Collector - Emitter Voltage		V _{CEO}	40	Vdc
Collector - Base Voltage		V _{CBO}	60	Vdc
Emitter – Base Voltage		V _{EBO}	6.0	Vdc
Collector Current – Continuous		I _C	200	mAdc
Electrostatic Discharge	HBM MM	ESD	>16000 >2000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



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NST3904DXV6T1

MARKING DIAGRAM



SOT-563 CASE 463A STYLE 1



MA = Device Code M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
NST3904DXV6T1G	SOT-563 (Pb-Free)	4000/Tape & Reel
NSVT3904DXV6T1G	SOT-563 (Pb-Free)	4000/Tape & Reel
NST3904DXV6T5G	SOT-563 (Pb-Free)	8000/Tape & Reel
SNST3904DXV6T5G	SOT-563 (Pb-Free)	8000/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

THERMAL CHARACTERISTICS

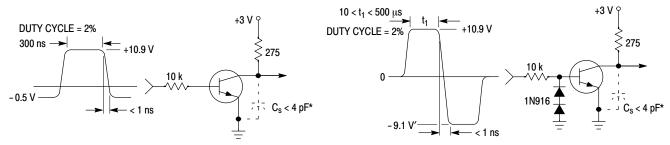
Characteristic (One Junction Heated)	Symbol	Max	Unit
Total Device Dissipation T _A = 25°C Derate above 25°C (Note 1)	P _D	357 2.9	mW mW/°C
Thermal Resistance Junction-to-Ambient (Note 1)	$R_{ heta JA}$	350	°C/W
Characteristic (Both Junctions Heated)	Symbol	Max	Unit
Total Device Dissipation T _A = 25°C Derate above 25°C (Note 1)	P _D	500 4.0	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{ heta JA}$	250	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

^{1.} FR-4 @ Minimum Pad

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

	Symbol	Min	Max	Unit		
OFF CHARACTERISTICS						
Collector - Emitter Breakdown Vo	oltage (Note 2) (I _C = 1.0 mAdc, I _B = 0)	V _{(BR)CEO}	40	_	Vdc	
Collector - Base Breakdown Volta	V _{(BR)CBO}	60	-	Vdc		
Emitter-Base Breakdown Voltag	$I_{E} = 10 \mu Adc, I_{C} = 0)$	V _{(BR)EBO}	6.0	_	Vdc	
Base Cutoff Current (V _{CE} = 30 V	dc, V _{EB} = 3.0 Vdc)	I _{BL}	_	50	nAdc	
Collector Cutoff Current (V _{CE} = 3	60 Vdc, V _{EB} = 3.0 Vdc)	I _{CEX}	_	50	nAdc	
ON CHARACTERISTICS (Note 2	2)					
$\begin{array}{c} \text{DC Current Gain} \\ \text{(I}_{C} = 0.1 \text{ mAdc, V}_{CE} = 1.0 \text{ Vd} \\ \text{(I}_{C} = 1.0 \text{ mAdc, V}_{CE} = 1.0 \text{ Vd} \\ \text{(I}_{C} = 10 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc} \\ \text{(I}_{C} = 50 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc} \\ \text{(I}_{C} = 100 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc} \\ \end{array}$	c) :) :)	h _{FE}	40 70 100 60 30	- 300 - -	-	
	·)	V _{CE(sat)}	_ _	0.2 0.3	Vdc	
Base-Emitter Saturation Voltage ($I_C = 10 \text{ mAdc}$, $I_B = 1.0 \text{ mAdc}$ ($I_C = 50 \text{ mAdc}$, $I_B = 5.0 \text{ mAdc}$	V _{BE(sat)}	0.65 -	0.85 0.95	Vdc		
SMALL-SIGNAL CHARACTER	ISTICS	·				
Current-Gain - Bandwidth Prod	uct (I _C = 10 mAdc, V _{CE} = 20 Vdc, f = 100 MHz)	f _T	300	-	MHz	
Output Capacitance (V _{CB} = 5.0 V	C _{obo}	_	4.0	pF		
Input Capacitance (V _{EB} = 0.5 Vd	c, I _C = 0, f = 1.0 MHz)	C _{ibo}	_	8.0	pF	
Input Impedance (V _{CE} = 10 Vdc,	h _{ie}	1.0 2.0	10 12	kΩ		
Voltage Feedback Ratio (V _{CE} = 1	h _{re}	0.5 0.1	8.0 10	X 10 ⁻⁴		
Small – Signal Current Gain (V _{CE}	h _{fe}	100 100	400 400	-		
Output Admittance (V _{CE} = 10 Vde	h _{oe}	1.0 3.0	40 60	μmhos		
Noise Figure ($V_{CE} = 5.0 \text{ Vdc}$, $I_{C} =$	NF		5.0 4.0	dB		
SWITCHING CHARACTERISTIC	cs	I	1	1	1	
Delay Time	$(V_{CC} = 3.0 \text{ Vdc}, V_{BE} = -0.5 \text{ Vdc})$	t _d	_	35		
Rise Time	(I _C = 10 mAdc, I _{B1} = 1.0 mAdc)	t _r	_	35	ns	
Storage Time	$(V_{CC} = 3.0 \text{ Vdc}, I_{C} = 10 \text{ mAdc})$	t _s	t _s – 200			
Fall Time	$(I_{B1} = I_{B2} = 1.0 \text{ mAdc})$	t _f –			ns	
		•				

^{2.} Pulse Test: Pulse Width \leq 300 μ s; Duty Cycle \leq 2.0%.



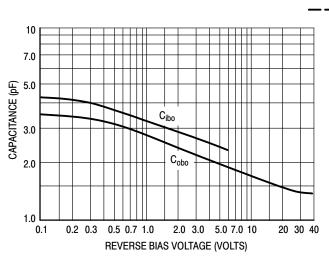
* Total shunt capacitance of test jig and connectors

Figure 1. Delay and Rise Time Equivalent Test Circuit

Figure 2. Storage and Fall Time Equivalent Test Circuit

TYPICAL TRANSIENT CHARACTERISTICS

- T_J = 25°C



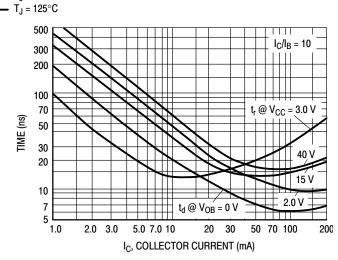
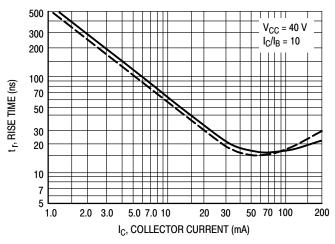


Figure 3. Capacitance

Figure 4. Turn - On Time





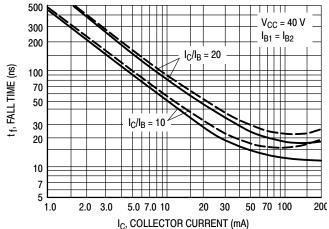
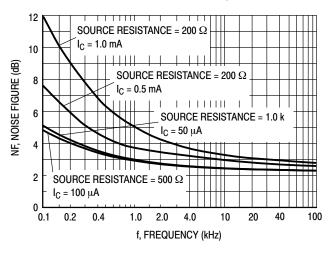


Figure 6. Fall Time

TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}\text{C}, Bandwidth = 1.0 \text{ Hz})$



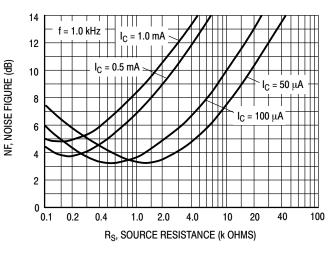
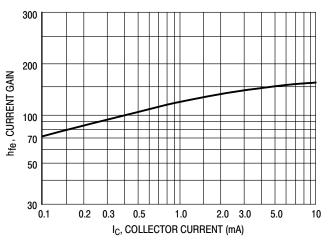


Figure 7. Noise Figure

Figure 8. Noise Figure

h PARAMETERS

 $(V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ kHz}, T_A = 25^{\circ}\text{C})$



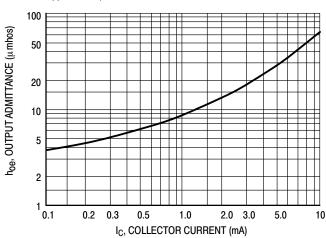


Figure 9. Current Gain

Figure 10. Output Admittance

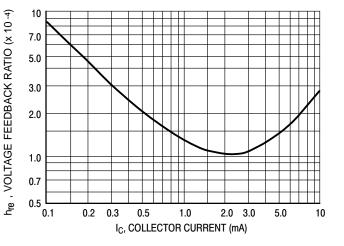


Figure 11. Input Impedance

IC, COLLECTOR CURRENT (mA)

Figure 12. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS

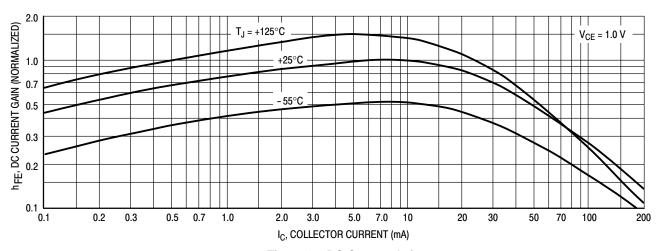


Figure 13. DC Current Gain

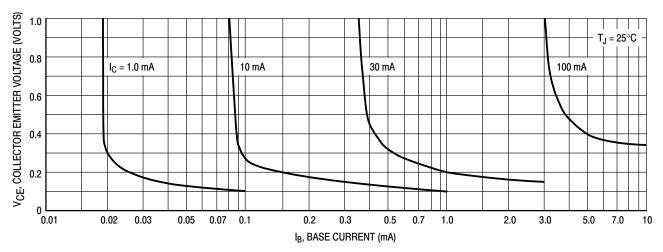


Figure 14. Collector Saturation Region

TYPICAL STATIC CHARACTERISTICS

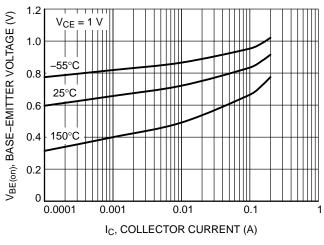


Figure 15. Base Emitter Voltage vs. Collector Current

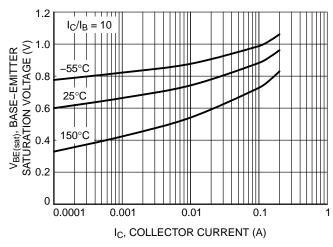


Figure 16. Base Emitter Saturation Voltage vs.
Collector Current

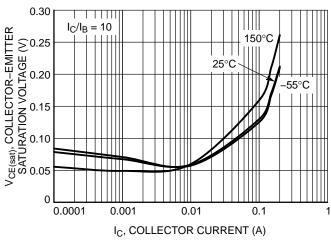


Figure 17. Collector Emitter Saturation Voltage vs. Collector Current

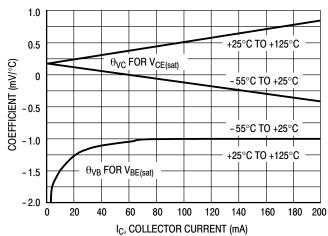
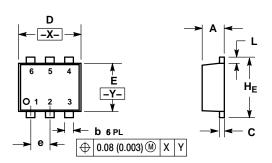


Figure 18. Temperature Coefficients

PACKAGE DIMENSIONS

SOT-563, 6 LEAD CASE 463A ISSUE F



NOTES

- 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

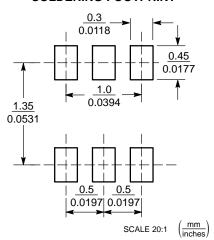
	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.50	0.55	0.60	0.020	0.021	0.023	
b	0.17	0.22	0.27	0.007	0.009	0.011	
С	0.08	0.12	0.18	0.003	0.005	0.007	
D	1.50	1.60	1.70	0.059	0.062	0.066	
Е	1.10	1.20	1.30	0.043	0.047	0.051	
е	0.5 BSC			0.02 BSC			
L	0.10	0.20	0.30	0.004	0.008	0.012	
HE	1.50	1.60	1.70	0.059	0.062	0.066	

STYLE 1: PIN 1. EMITTER 1

2. BASE 1 3. COLLECTOR 2 4. EMITTER 2

5. BASE 2 6. COLLECTOR 1

SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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